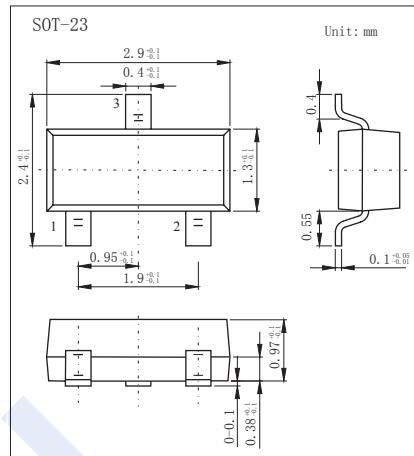
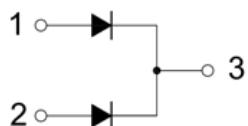


Schottky Diodes**RB495D (KB495D)****■ Features**

- Small surface mounting type
- Low Forward Voltage
- Low Reverse Current
- High Reliability

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V _{RRM}	40	V
Working Peak Reverse Voltage	V _{RWM}	40	
RMS Reverse Voltage	V _{R(RMS)}	28	
Average Rectified Output Current	I _O	0.4	A
Non-repetitive Peak Forward Surge Current	I _{FSM}	2	
Power Dissipation	P _D	250	mW
Thermal Resistance Junction to Ambient	R _{θ JA}	400	°C/W
Junction Temperature	T _J	125	°C
Storage Temperature range	T _{Stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 100 uA	40			V
Forward voltage	V _F	I _F = 10mA			0.3	
		I _F = 200mA			0.5	
Reverse voltage leakage current	I _R	V _R =25 V			70	uA

■ Marking

Marking	D3Q
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